

-60V P+P-Channel Enhancement Mode MOSFET

MAIN CHARACTERISTICS

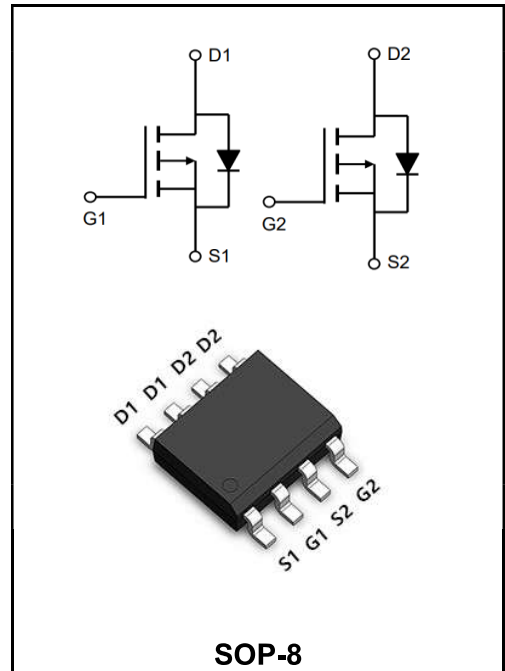
I_D	-3.4A
V_{DSS}	-60V
R_{DS(ON)-typ(@V_{GS}=-10V)}	<110mΩ(Typ:90mΩ)

DESCRIPTION

The YFW3V06S uses advanced trench technology to provide excellent R_{DS(ON)}, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

APPLICATIONS

- ◆ Battery protection
- ◆ Load switch
- ◆ Uninterruptible power supply



Absolute Maximum Ratings (T_c=25°C unless otherwise noted)

Parameter	Symbol	Value	Units
Drain-Source Voltage	V_{DS}	-60	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current, V _{GS} @ -10V ¹ @T _c =25°C	I_D	-3.4	A
Continuous Drain Current, V _{GS} @ -10V ¹ @T _c =70 °C	I_D	-2.7	A
Pulsed Drain Current ²	I_{DM}	-27	A
Single Pulse Avalanche Energy ³	E_{AS}	29.8	mJ
Avalanche Current	I_{AS}	-24.4	A
Total Power Dissipation ⁴ @T _A =25°C	P_D	2	W
Operating Junction Temperature Range	T_J	-55 to 150	°C
Storage Temperature Range	T_{STG}	-55 to 150	°C
Thermal Resistance Junction-Ambient ¹	R_{θJA}	62	°C/W

P-Channel Electrical Characteristics (T_J =25°C, unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =-250uA	BV_{DSS}	-60	-	-	V
BV _{DSS} Temperature Coefficient	Reference to 25°C , I _D =-1mA	$\Delta BV_{DSS}/\Delta T_J$	-	-0.03	-	V/°C
Static Drain-Source On-Resistance ²	V _{GS} =-10V , I _D =-10A	R_{DS(ON)}	-	90	110	mΩ
	V _{GS} =-4.5V , I _D =-5A		-	110	130	
Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =-250uA	V_{GS(th)}	-1.0	-1.7	-2.5	V
Drain-Source Leakage Current	V _{DS} =-48V , V _{GS} =0V , T _J =25°C	I_{DSS}	-	-	1	uA
	V _{DS} =-48V , V _{GS} =0V , T _J =55°C		-	-	5	
Gate-Source Leakage Current	V _{GS} =±20V , V _{DS} =0V	I_{GSS}	-	-	±100	nA
Forward Transconductance	V _{DS} =-5V , I _D =-3A	g_{fs}	-	8.5	-	S
Total Gate Charge (-4.5V)	V _{DS} =-48V V _{GS} =-4.5V I _D =-3A	Q_g	-	18	-	nC
Gate-Source Charge		Q_{gs}	-	4.0	-	
Gate-Drain Charge		Q_{gd}	-	5.2	-	
Turn-On Delay Time	V _{DD} =-15V V _{GS} =-10V R _G =3.3Ω I _D =-1A	t_{d(on)}	-	9.0	-	ns
Rise Time		T_r	-	15	-	
Turn-Off Delay Time		t_{d(OFF)}	-	33	-	
Fall Time		t_f	-	12	-	
Input Capacitance	V _{DS} =-15V V _{GS} =0V f=1MHz	C_{iss}	-	978	-	pF
Output Capacitance		C_{oss}	-	51	-	
Reverse Transfer Capacitance		C_{rss}	-	39	-	
Continuous Source Current ^{1,5}	V _G =V _D =0V , Force Current	I_s	-	-	-3.4	A
Diode Forward Voltage ²	V _{GS} =0V , I _S =-1A , T _J =25°C	V_{SD}	-	-	-1.2	V

Note:

- 1.The data tested by surface mounted on a 1 inch 2 FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width \cong 300us , duty cycle \cong 2%
- 3.The EAS data shows Max. rating . The test condition is V_{DD} =-25V, V_{GS} =-10V, L=0.1mH, I_{AS} =-24A
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I D and I DM , in real applications , should be limited by total power dissipation.

P-Channel Typical Characteristics

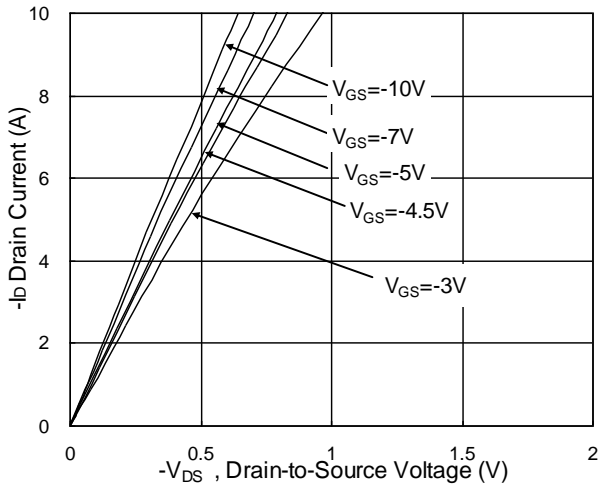


Fig.1 Typical Output Characteristics

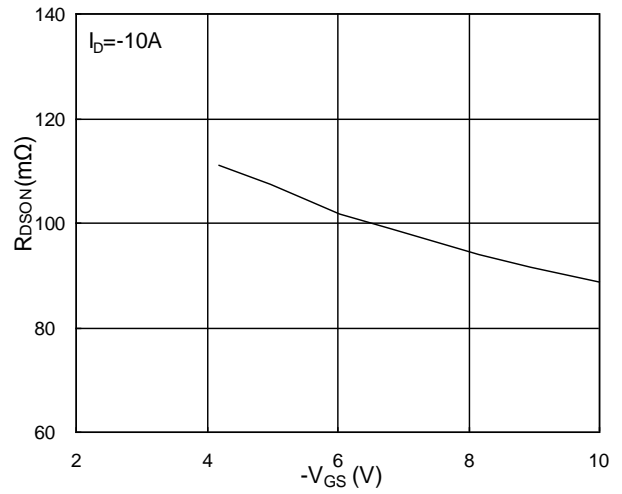


Fig.2 On-Resistance v.s Gate-Source

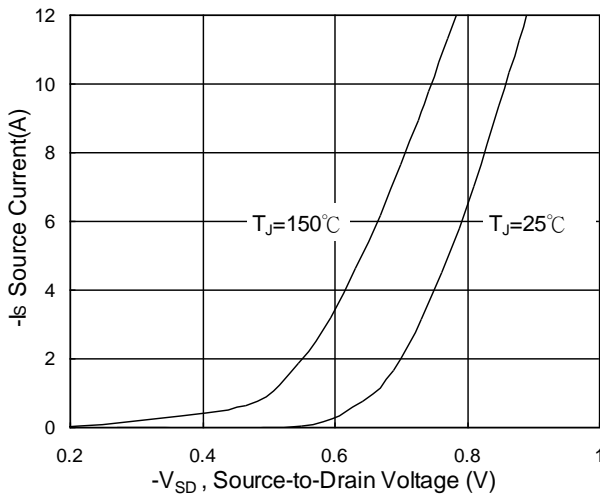


Fig.3 Forward Characteristics of Reverse

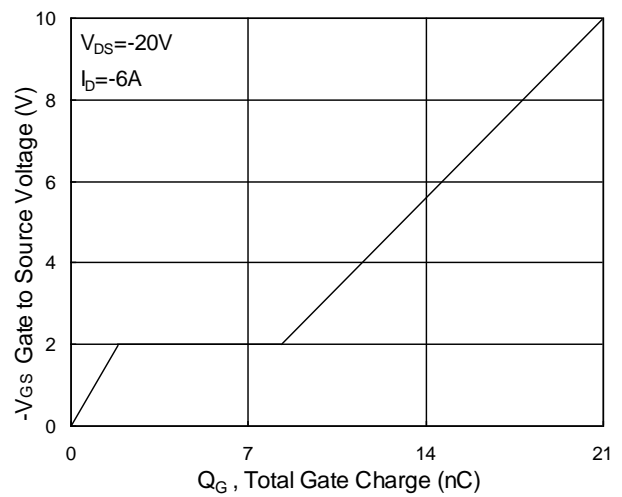


Fig.4 Gate-Charge Characteristics

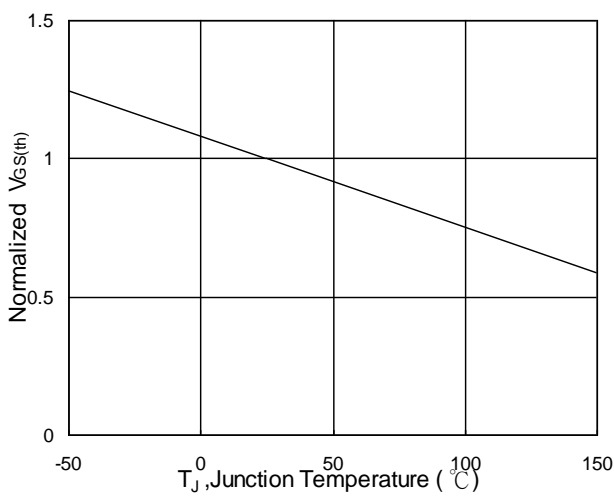


Fig.5 Normalized $V_{GS(th)}$ v.s T_J

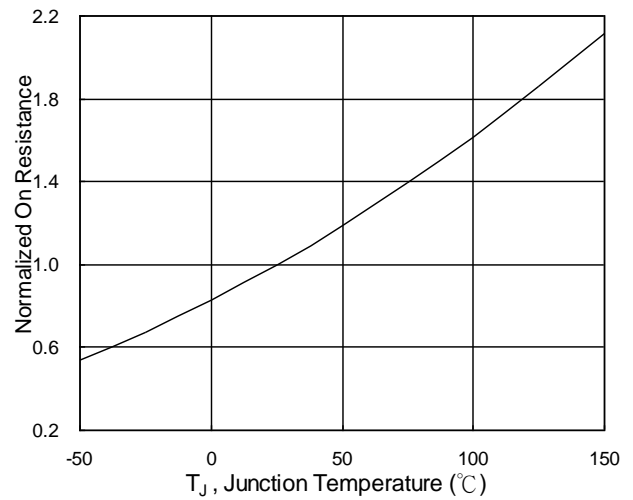


Fig.6 Normalized $R_{DS(on)}$ v.s T_J

P-Channel Typical Characteristics

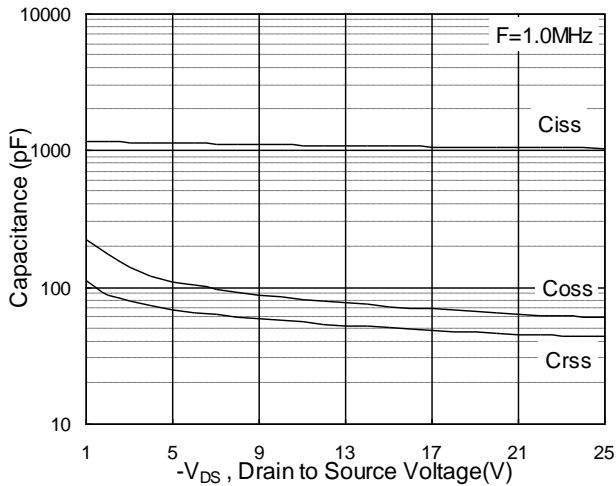


Fig.7 Capacitance

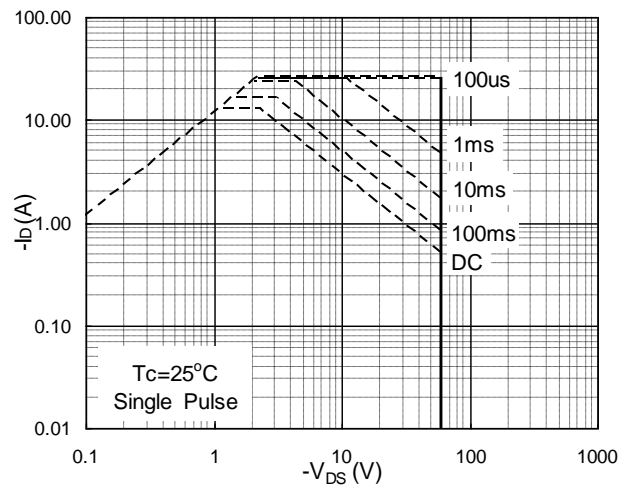


Fig.8 Safe Operating Area

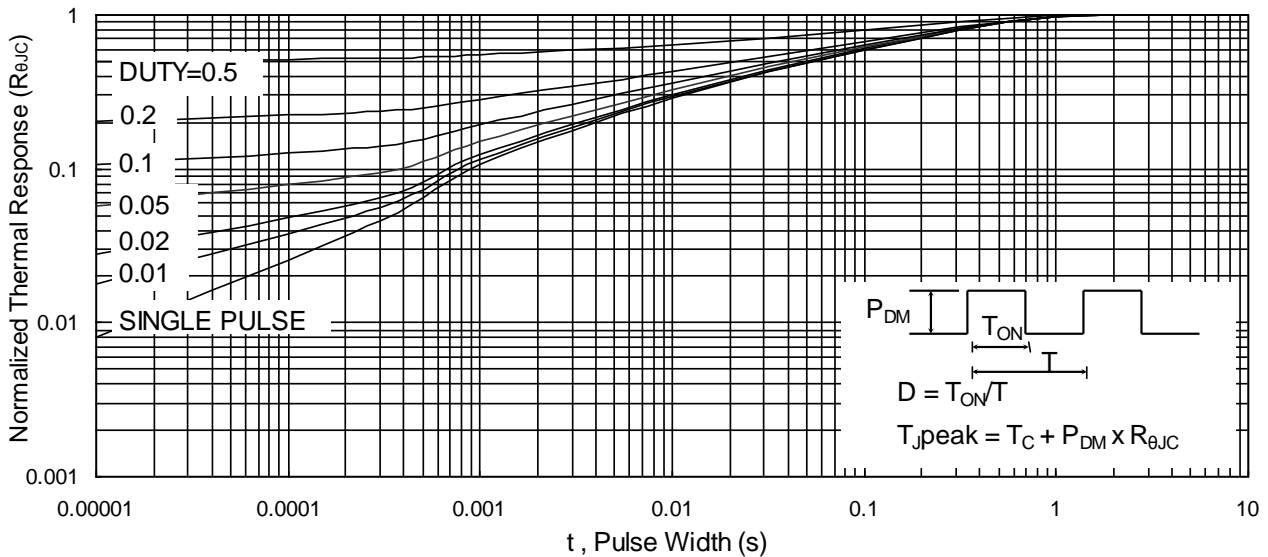


Fig.9 Normalized Maximum Transient Thermal Impedance

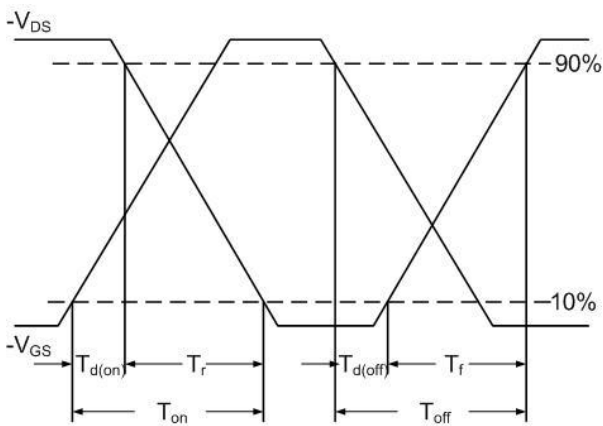


Fig.10 Switching Time Waveform

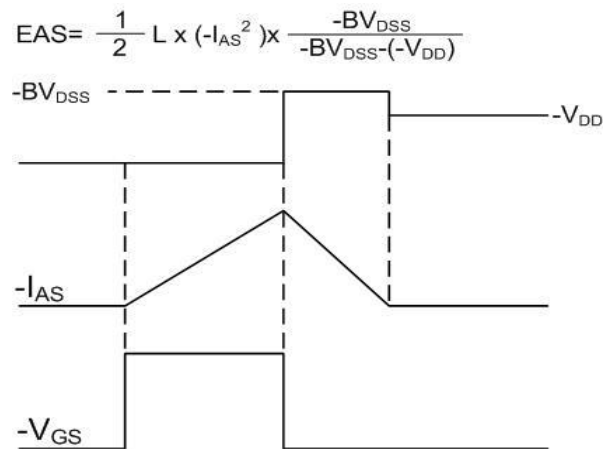
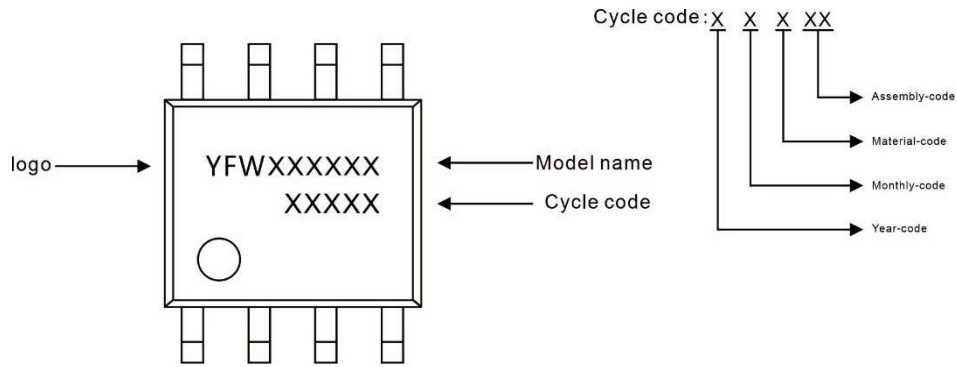


Fig.11 Unclamped Inductive Switching Waveform

Marking Diagram



Ordering information

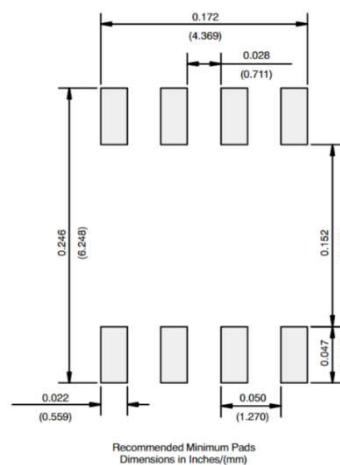
Package	Packing Description	Packing Quantity
SOP-8	Tape/Reel, 13" reel	3000PCS/Reel 30000PCS/Carton

Package Dimensions

SOP-8

Dim	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	1.35	1.75	0.053	0.069
A1	0.10	0.25	0.004	0.010
A2	1.35	1.50	0.053	0.059
b	0.35	0.55	0.014	0.022
c	0.15	0.25	0.006	0.010
D	4.80	5.00	0.189	0.197
D1	3.10	3.50	0.122	0.138
E	5.80	6.20	0.228	0.244
E1	3.80	4.00	0.150	0.157
E2	2.20	2.60	0.087	0.102
e	1.27 (BSC)		0.050 (BSC)	
L	0.40	1.27	0.016	0.050
θ	0°	8°	0°	8°

The recommended mounting pad size



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